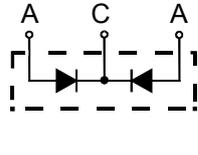
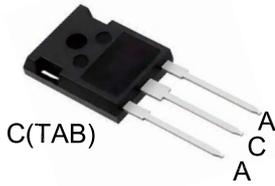


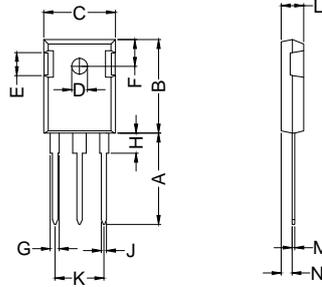
HUR3020PT, HUR3030PT, HUR3040PT

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.620	0.640
ØD	3.15	3.65	0.124	0.144
E	4.32	5.49	0.170	0.216
F	5.40	6.30	0.213	0.248
G	1.65	2.18	0.065	0.086
H	3.80	4.50	0.150	0.177
J	1.00	1.40	0.039	0.055
K	10.80	11.10	0.425	0.437
L	4.70	5.30	0.185	0.209
M	0.40	0.80	0.016	0.031
N	1.50	2.49	0.059	0.098

	V _{RSM} V	V _{RRM} V
HUR3020PT	200	200
HUR3030PT	300	300
HUR3040PT	400	400



Symbol	Test Conditions	Maximum Ratings	Unit
I _{FRMS} I _{FAVM}	T _C =135°C; rectangular, d=0.5	35 2 x 15	A
I _{FSM}	T _{VJ} =45°C; t _p =10ms (50Hz), sine	140	A
E _{AS}	T _{VJ} =25°C; non-repetitive; I _{AS} =2.5A; L=180uH	0.8	mJ
I _{AR}	V _A =1.5·V _R typ.; f=10kHz; repetitive	0.3	A
T _{VJ} T _{VJM} T _{stg}		-55...+175 175 -55...+150	°C
P _{tot}	T _C =25°C	95	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	6	g

HUR3020PT, HUR3030PT, HUR3040PT

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I _R	T _{VJ} =25°C; V _R =V _{RRM} T _{VJ} =150°C; V _R =V _{RRM}		100	uA
			0.5	mA
V _F	I _F =15A; T _{VJ} =150°C T _{VJ} =25°C		200/300	V
			400	
		0.95	1.00	
		1.00	1.08	
R _{thJC} R _{thCH}		0.5	1.6	K/W
t _{tr}	I _F =1A; -di/dt=100A/us; V _R =30V; T _{VJ} =25°C	30		ns
I _{RM}	V _R =100V; I _F =25A; -di _F /dt=100A/us; T _{VJ} =100°C		2.7	A

FEATURES

- * International standard package
- * Planar passivated chips
- * Very short recovery time
- * Extremely low switching losses
- * Low I_{RM}-values
- * Soft recovery behaviour
- * RoHS compliant

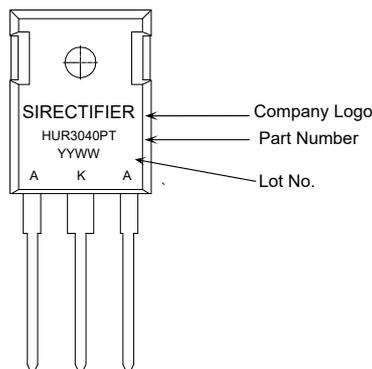
APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Antisaturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * Avalanche voltage rated for reliable operation
- * Soft reverse recovery for low EMI/RFI
- * Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

MARKING



ORDERING INFORMATION

Part Number	Package	Shipping	Marking Code
HUR3020PT	TO-247AD	30pcs / Tube	HUR3020PT
HUR3030PT	TO-247AD	30pcs / Tube	HUR3030PT
HUR3040PT	TO-247AD	30pcs / Tube	HUR3040PT

Sirectifier®

HUR3020PT, HUR3030PT, HUR3040PT

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

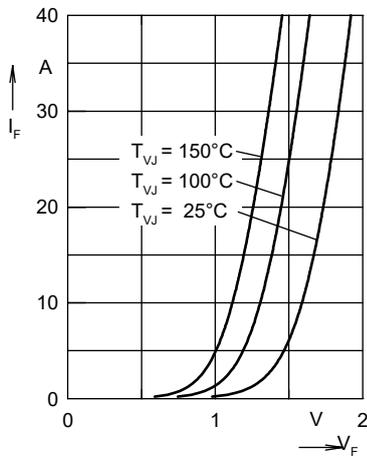


Fig. 1 Forward current I_F versus V_F

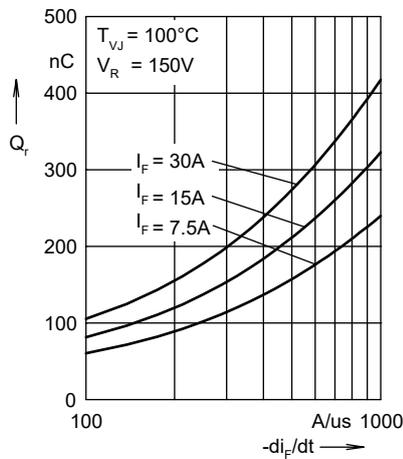


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

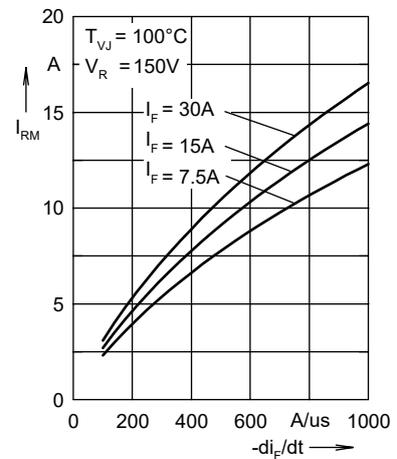


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

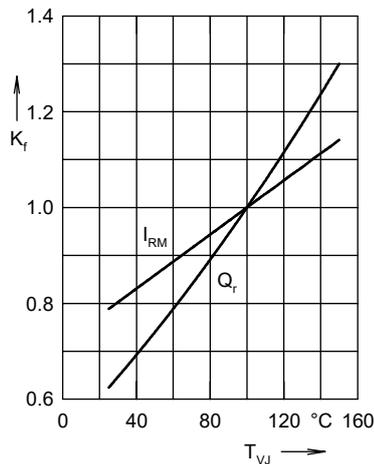


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

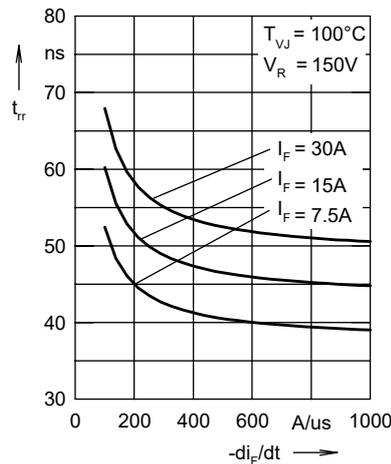


Fig. 5 Recovery time t_{tr} versus $-di_F/dt$

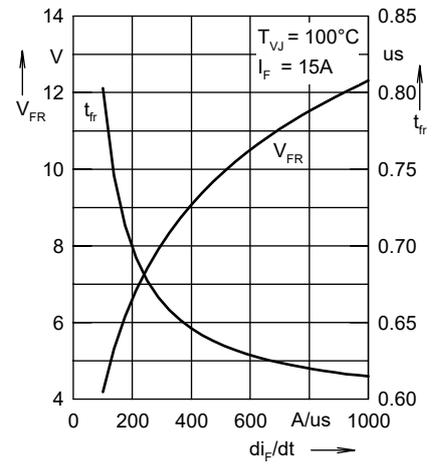


Fig. 6 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

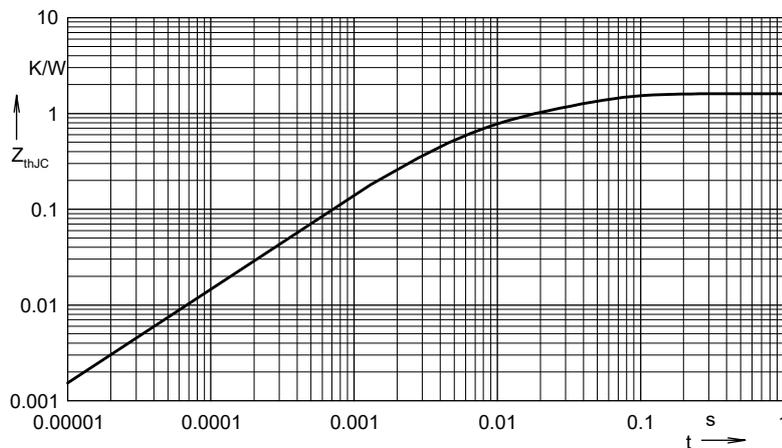


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.908	0.005
2	0.35	0.0003
3	0.342	0.017